

Prof Sir Colin Humphreys

CBE, FEng, FRS, BSc, MA, PhD, Hon DSc, FIMMM, FInstP, FCGI, Hon FRMS

School of Engineering and Materials Science
Queen Mary University of London
Mile End Road
London E1 4NS

tel: +44 (0)20 7882 3450

email: c.humphreys@qmul.ac.uk web: www.sems.qmul.ac.uk/c.humphreys

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